

In the Claims:

Claims 1-3 (*Cancelled*)

4. (*Currently Amended*) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen as a carrier gas,

~~A method as claimed in claim 2;~~ wherein the epitaxial layer comprises a SiGe epitaxial layer.

5. (*Currently Amended*) ~~A method as claimed in claim 2;~~ The method as claimed in claim 4, wherein the epitaxial layer further comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.

6. (*Cancelled*)

7. (*Currently Amended*) ~~A method as claimed in claim 2;~~ The method as claimed in claim 4, which is carried out at a temperature that facilitates a CVD growth rate of an epitaxial layer that is substantially greater than a CVD growth rate of such an epitaxial layer using hydrogen as a carrier gas.

8. (*Cancelled*)

Claims 9-16 (*Cancelled*)

17. (*Cancelled*)

18. (*Previously presented*) A method as claimed in claim 4, which is carried out at a temperature of less than about 600°C.

19. *(Previously presented)* A method as claimed in claim 5, which is carried out at a temperature of less than about 600°C.

20. *(Cancelled)*